

Supporting information

Synthesis and optoelectronic properties of reduced graphene oxide/InP quantum dot hybrids

Guohua Jiang,^{ab} Yanjie Su,^{*a} Ming Li,^a Jing Hu,^a Bo Zhao,^{*b} Zhi Yang,^a and Hao Wei^{*a}

^a Key Laboratory for Thin Film and Microfabrication of the Ministry of Education, Department of Micro/Nano Electronics, School of Electronics, Information and Electrical Engineering, Shanghai Jiao Tong University, Shanghai 200240, PR China. Email: yanjiesu@sjtu.edu.cn, haowei@sjtu.edu.cn.

^b Jiangsu Key Laboratory of Advanced Laser Materials and Devices, School of Physics and Electronic Engineering, Jiangsu Normal University, Xuzhou 221116, PR China. Email: phyzhaobo@jsnu.edu.cn.

Figure S1

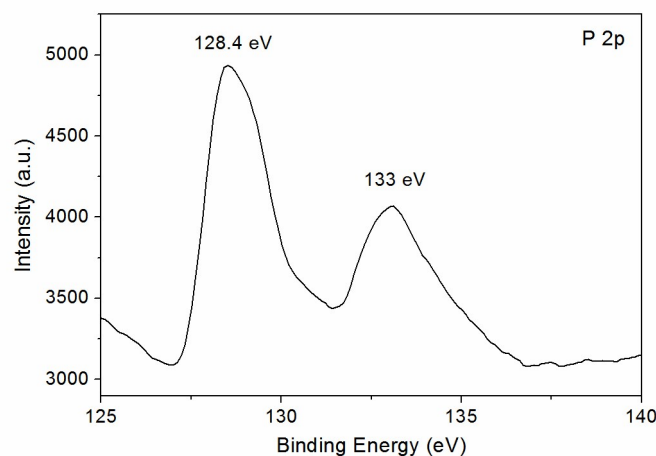


Figure S1. High resolution P_{2p} XPS spectrum of the rGO/InP QD hybrids

Figure S2

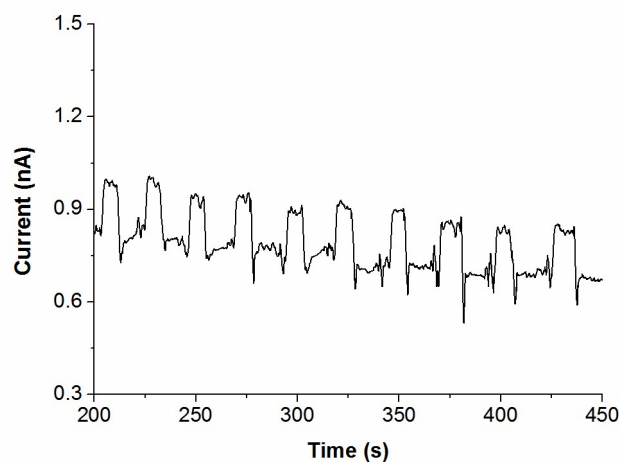


Figure S2. The current response of pure InP QDs versus time under intermittent blue light irradiation with a voltage of 1 V.